ARR-BMXXX-CA8

DESCARGADOR GASEOSO

Gas Discharge Tube

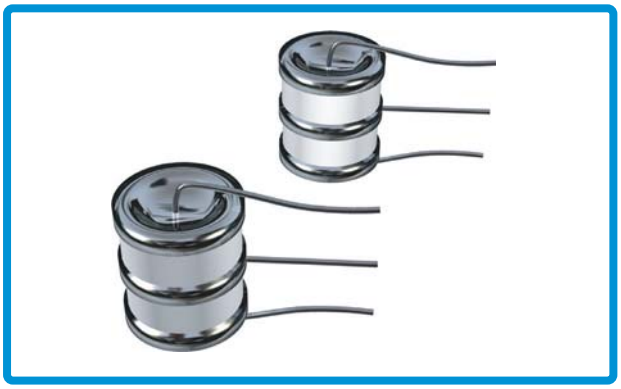
SYC SEMICONDUCTORES Y COMPONENTES

FEATURE

- Rugged Ceramic-Metal Construction
- Available With Fail-Safe Clip
- Available With Or Without Leads
- Available With Various Lead Spacing
- Low capacitance (< 2pF)
- Large Transient Current Absorbing Capability

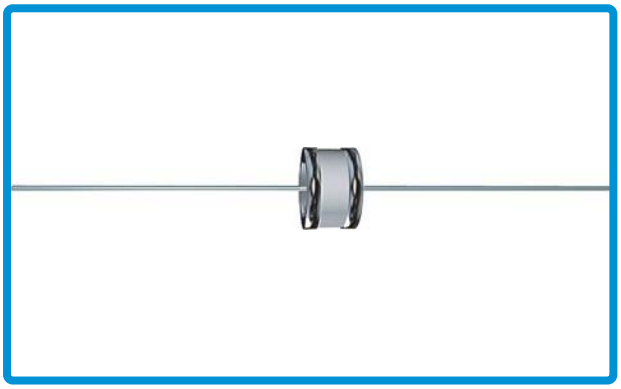
APPLICATIONS

- Repeaters, Modems
- Telephone Interface, Line Cards
- Data Communication Equipment
- Line Test Equipment



CHARACTERISTICS

- Two or three electrodes
- Discharge voltage: 70V to 800V
- 5.5mm or 8mm diameter



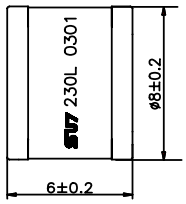
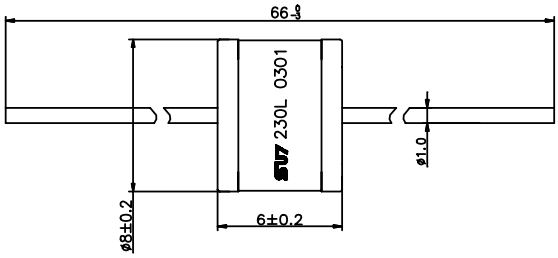
RoHS

SYC SEMICONDUCTORES Y COMPONENTES

2-Electrode MGT (Φ 8.0×6.0)

20KA/20A/200A

Dimensions: mm

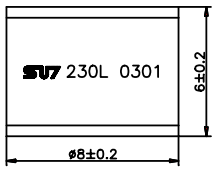
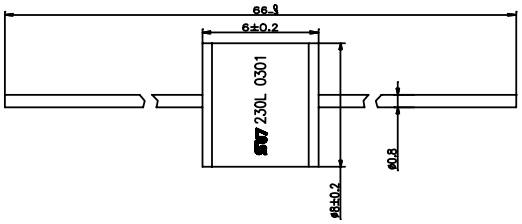
MGT-AP****-CA8	MGT-BP****-CA8
	

Item	Parts Number						
Without Lead	MGT-AP075M-CA8	MGT-AP090M-CA8	MGT-AP150M-CA8	MGT-AP230M-CA8	MGT-AP350M-CA8	MGT-AP470M-CA8	MGT-AP600M-CA8
Axial Leaded	MGT-BP075M-CA8	MGT-BP090M-CA8	MGT-BP150M-CA8	MGT-BP230M-CA8	MGT-BP350M-CA8	MGT-BP470M-CA8	MGT-BP600M-CA8
DC Breakdown Voltage (@100V/S) (V)	75	90	150	230	350	470	600
Tolerance of DCBV	±20%	±20%	±20%	±20%	±20%	±20%	±20%
Impulse Breakdown Voltage (@1KV/μS) (V)	≤650	≤650	≤650	≤700	≤900	≤1000	≤1200
AC Discharge Current (@50HZ) (A)	20	20	20	20	20	20	20
Surge Discharge Current (@10/1000μs) (A)	200	200	200	200	200	200	200
Surge Discharge Current (@8/20μs) (KA)	20	20	20	20	20	20	20
Insulation Resistance (MΩ)	≥10000	≥10000	≥10000	≥10000	≥10000	≥10000	≥10000
Electrode Capacitance (@1MHZ) (pF)	≤1.5	≤1.5	≤1.5	≤1.5	≤1.5	≤1.5	≤1.5
Note							

2-Electrode MGT(Φ 8.0 $\times$ 6.0)

10KA/10A/100A

Dimensions: mm

MGT-AM****-CA8	MGT-BM****-CA8
	

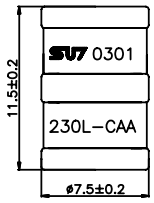
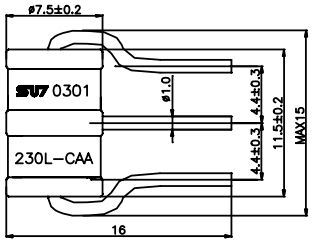
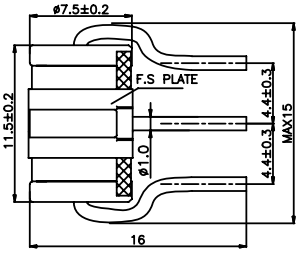
Item	Parts Number						
Without Lead	MGT-AM075M-CA8	MGT-AM090M-CA8	MGT-AM150M-CA8	MGT-AM230M-CA8	MGT-AM350M-CA8	MGT-AM470M-CA8	MGT-AM600M-CA8
Axial Leaded	MGT-BM075M-CA8	MGT-BM090M-CA8	MGT-BM150M-CA8	MGT-BM230M-CA8	MGT-BM350M-CA8	MGT-BM470M-CA8	MGT-BM600M-CA8
DC Breakdown Voltage (@100V/S) (V)	75	90	150	230	350	470	600
Tolerance of DCBV	±20%	±20%	±20%	±20%	±20%	±20%	±20%
Impulse Breakdown Voltage (@1KV/μS) (V)	≤650	≤650	≤650	≤700	≤900	≤1000	≤1200
AC Discharge Current (@50HZ) (A)	10	10	10	10	10	10	10
Surge Discharge Current (@10/1000μs) (A)	100	100	100	100	100	100	100
Surge Discharge Current (@8/20μs) (KA)	10	10	10	10	10	10	10
Insulation Resistance (MΩ)	≥10000	≥10000	≥10000	≥10000	≥10000	≥10000	≥10000
Electrode Capacitance (@1MHZ) (pF)	≤1.5	≤1.5	≤1.5	≤1.5	≤1.5	≤1.5	≤1.5
Note							

SYC SEMICONDUCTORES Y COMPONENTES

3-Electrode MGT (ϕ 7.5 × 11.5)

10KA/10A/100A

Dimensions: mm

MGT-SM****-CAA	MGT-MM****-CAA	MGT-MM****-FAA
		

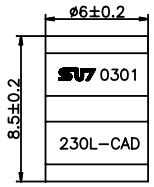
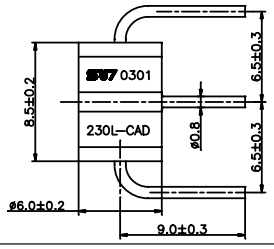
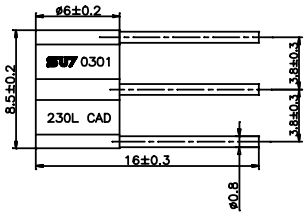
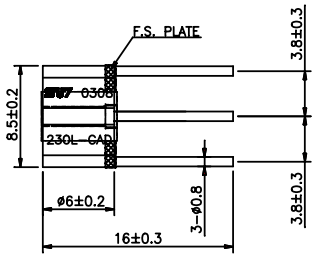
Item	Parts Number						
Without Lead	MGT-SM075M-CAA	MGT-SM090M-CAA	MGT-SM150M-CAA	MGT-SM230M-CAA	MGT-SM350M-CAA	MGT-SM470M-CAA	MGT-SM600M-CAA
Axial Leaded	MGT-MM075M-CAA	MGT-MM090M-CAA	MGT-MM150M-CAA	MGT-MM230M-CAA	MGT-MM350M-CAA	MGT-MM470M-CAA	MGT-MM600M-CAA
Leaded w/Fail Safe	MGT-MM075M-FAA	MGT-MM090M-FAA	MGT-MM150M-FAA	MGT-MM230M-FAA	MGT-MM350M-FAA	MGT-MM470M-FAA	MGT-MM600M-FAA
DC Breakdown Voltage (@100V/S) (V)	75	90	150	230	350	470	600
Tolerance of DCBV	±20%	±20%	±20%	±20%	±20%	±20%	±20%
Impulse Breakdown Voltage (@1KV/μS) (V)	≤650	≤650	≤650	≤700	≤900	≤1000	≤1200
AC Discharge Current (@50HZ) (A)	10	10	10	10	10	10	10
Surge Discharge Current (@10/1000μs) (A)	100	100	100	100	100	100	100
Surge Discharge Current (@8/20μs) (KA)	10	10	10	10	10	10	10
Insulation Resistance (MΩ)	≥10000	≥10000	≥10000	≥10000	≥10000	≥10000	≥10000
Electrode Capacitance (@1MHZ) (pF)	≤1.5	≤1.5	≤1.5	≤1.5	≤1.5	≤1.5	≤1.5
Note							

SYC SEMICONDUCTORES Y COMPONENTES

3-Electrode MGT(Φ6×8.5)

10KA/10A/100A

Dimensions: mm

MGT-SM****-CAD	MGT-MM****-CAD	MGT-NM***-CAD	MGT-MM****-FAD
			

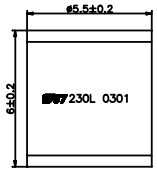
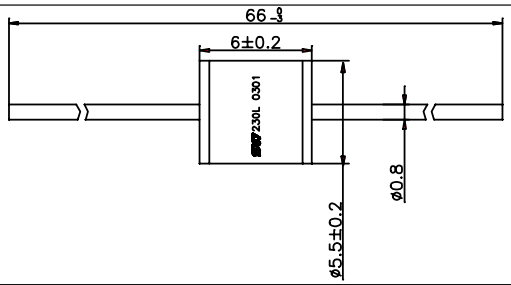
Item	Parts Number						
Without Lead	MGT-SM075M-CAD	MGT-SM090M-CAD	MGT-SM150M-CAD	MGT-SM230M-CAD	MGT-SM350M-CAD	MGT-SM470M-CAD	MGT-SM600M-CAD
Axial Leaded	MGT-MM075M-CAD	MGT-MM090M-CAD	MGT-MM150M-CAD	MGT-MM230M-CAD	MGT-MM350M-CAD	MGT-MM470M-CAD	MGT-MM600M-CAD
Axial Leaded	MGT-NM075M-CAD	MGT-NM090M-CAD	MGT-NM150M-CAD	MGT-NM230M-CAD	MGT-NM350M-CAD	MGT-NM470M-CAD	MGT-NM600M-CAD
Leaded w/Fail Safe	MGT-MM075M-FAD	MGT-MM090M-FAD	MGT-MM150M-FAD	MGT-MM230M-FAD	MGT-MM350M-FAD	MGT-MM470M-FAD	MGT-MM600M-FAD
DC Breakdown Voltage (@100V/S) (V)	75	90	150	230	350	470	600
Tolerance of DCBV	±20%	±20%	±20%	±20%	±20%	±20%	±20%
Impulse Breakdown Voltage (@1KV/μS) (V)	≤650	≤650	≤650	≤700	≤900	≤1000	≤1200
AC Discharge Current (@50HZ) (A)	10	10	10	10	10	10	10
Surge Discharge Current (@10/1000μs) (A)	100	100	100	100	100	100	100
Surge Discharge Current (@8/20μs) (KA)	10	10	10	10	10	10	10
Insulation Resistance (MΩ)	≥10000	≥10000	≥10000	≥10000	≥10000	≥10000	≥10000
Electrode Capacitance (@1MHZ) (pF)	≤1.5	≤1.5	≤1.5	≤1.5	≤1.5	≤1.5	≤1.5
Note							

SYC SEMICONDUCTORES Y COMPONENTES

2-Electrode MGT (ϕ 5.5 × 6.0)

5KA/5A/100A

Dimensions: mm

MGT-AL****-CA5	MGT-BL****-CA5
	

Item	Parts Number						
Without Lead	MGT-AL75M-CA5	MGT-AL090M-CA5	MGT-AL150M-CA5	MGT-AL230M-CA5	MGT-AL350M-CA5	MGT-AL470M-CA5	MGT-AL600M-CA5
Axial Leaded	MGT-BL075M-CA5	MGT-BL090M-CA5	MGT-BL150M-CA5	MGT-BL230M-CA5	MGT-BL350M-CA5	MGT-BL470M-CA5	MGT-BL600M-CA5
DC Breakdown Voltage (@100V/S) (V)	75	90	150	230	350	470	600
Tolerance of DCBV	±20%	±20%	±20%	±20%	±20%	±20%	±20%
Impulse Breakdown Voltage (@1KV/μS) (V)	≤650	≤650	≤650	≤700	≤900	≤1000	≤1200
AC Discharge Current (@50HZ) (A)	5	5	5	5	5	5	5
Surge Discharge Current (@10/1000μs) (A)	100	100	100	100	100	100	100
Surge Discharge Current (@8/20μs) (KA)	5	5	5	5	5	5	5
Insulation Resistance (MΩ)	≥10000	≥10000	≥10000	≥10000	≥10000	≥10000	≥10000
Electrode Capacitance (@1MHZ) (pF)	≤1.5	≤1.5	≤1.5	≤1.5	≤1.5	≤1.5	≤1.5
Note							